

2004 IEEE SEMI-CONDUCTING & INSULATING MATERIALS CONFERENCE (SIMC)

The 13th IEEE Semi-conducting and insulating Materials Conference (SIMC-XIII 2004) will be held 20-25 September 2004 in Beijing, China. The SIMC is a series of biennial conferences initiated in 1980 in Nottingham (UK). SIMC will continue its tradition of highlighting the fundamental materials problems of compound semiconductors, which are widely used for electronic and optoelectronic devices. Beijing is a city of contrasts. On one hand, it's fast becoming a modern city of first-class hotels, business centers, shopping malls and wide avenues.

On the other hand, there are the Hutongs, those ageless communities of narrow streets that have changed little over the past 700 years.

An important purpose of the meeting is to provide an opportunity for scientists and engineers from both the academic sphere and industry to meet together for an efficient scientific



exchange. The following seven topical areas comprise the scope of the Conference:

- Semi-insulating III-V compounds,
- Non-Stoichiometric III-V compounds
- Narrow band gap nitrides such as GaAsN and GaAsPN etc,

- Wide gap materials such as GaN, AlGaIn, AlGaN, SiC and ZnO etc,
- Nanomaterials and technologies
- Novel materials
- All kinds of devices emerging from the above materials.

The IEEE Electron Devices Society, the Chinese Academy of Sciences, and the National Natural Science Foundation of China, sponsor the conference. For additional conference program and registration information, please view our website at <http://simc.semi.ac.cn:6666/> or contact Conference Chairman, Prof. Zhanguo Wang, at: Tel: 0086-10-82304250; Fax: 0086-10-82305002; Email: zgwang@red.semi.ac.cn.

*Zhanguo Wang, SIMC General Chair
Key Laboratory of Semiconductor
Materials Science
Institute of Semiconductors, CAS, China*

2004 IEEE SYMPOSIUM ON VLSI TECHNOLOGY

The 24th Annual Symposium on VLSI Technology will be held in the beautiful city of Honolulu, Hawaii June 15-17, 2004. The Japan Society of Applied Physics (JSAP) and the IEEE Electron Devices Society (EDS) jointly sponsor the Symposium on VLSI Technology.

The conference will be held in the Hilton Hawaiian Village and begins with a one-day short course held on Monday, June 14, 2004. This is followed by three days of technical sessions held June 15-17, 2004. The technical sessions commence with a plenary session given by distinguished invited speakers, and then continue with presentations of submitted technical papers. Evening "Rump Sessions" on topics of current technical interest will also be held. A banquet will be held on the evening of Tuesday, June 15, 2004.

The Symposium welcomes the submission of papers on all aspects



of VLSI Technology. The scope of the Symposium includes:

- New concepts and breakthroughs in VLSI devices and processes
- New functional devices including quantum effect devices with possible VLSI implementation
- Materials innovation for MOSFET and interconnect in VLSI
- Advanced lithography and fine pat-

terning technologies for high density VLSI

- Process/Device modeling of VLSI devices
- Packaging and reliability of VLSI devices
- Theories and fundamentals related to the above devices
- New concepts and technologies for VLSI manufacturing

Two technical committees consisting of technical experts from industry and academia review submitted technical papers. These two committees are a North America and Europe (NAE) committee, and a Japan and the Far East (JFE) committee. Based on the combined ranking of these two committees, the best papers are selected and organized into technical sessions.

One of the strengths of the Symposium on VLSI Technology is its association with the Symposium on VLSI Circuits, which is held each year at the same location during the same